KK2000-FAST SWITCHING THYRISTOR

1800-2000 V_{DRM}

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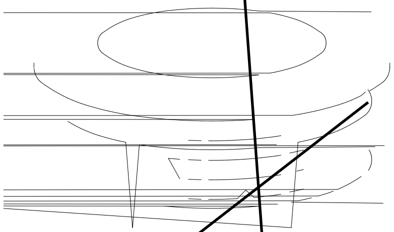
HIGH POWER THYRISTOR FOR INVERTER APPLICATION

Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability up to 2000 volts
- . High dv/dt Capability
- . Pressure Assembled Device



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ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KK2000/18	1800	1800	2000
KK2000/20	2000	2000	2100

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 80 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/µs

Conducting - On State

ELECTRICAL CHARACTERISTICS AND RATINGS KK2000-FAST SWITCHING THYRISTOR

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	V_D=12V;R_L=3ohms;T_j=+25ºC
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_D;R